Atty. Docket No.: Serial No.: 09/973.240								-								
FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Ute several sheets if nocessary) REFERENCE DESIGNATION U.S. PATENT DOCUMENTS Partial Translation Filing Date: (Ctass Subctass Filing Date if Appropriate if Approp	Form P	TO-14	149 (N	1odifi	ed)		•,	. •				o.:				
Class Subclass Filing Date: Class Class Filing Date: Class Class Filing Date: Class Class Class Filing Date: Class Class Class Filing Date: Class Cl				FO	R AP	PLIC	ANT'	'S			Applicants: Rar	ıgarajan, e	t al.			
Date Name Class Subclass Filing Date	OIP	, y _C						sary)			October 9, 2001		2121			
Date Name Class Subclass Filing Dute Appropriate Appropri	a b	2002	<u>.</u>					· R	REFERENC	E DESI	GNATION U.S	. PATEN	r docun	IENT:	5	
FOREIGN PATENT DOCUMENTS FOREIGN PATENT DOCUMENTS FAMILIA ART (Including Author, Title, Date, Pertinent Pages, etc.) Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.	Examiner Soitial	Do	ment N	Vumber					Date	Name		Class	Subclass	if		
FOREIGN PATENT DOCUMENTS FOREIGN PATENT DOCUMENTS Examiner Initial OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.	Son	5	9	0	5	0	2	0	5/18/99	Hu, et	al.	430	394	12/2	0/96	
FOREIGN PATENT DOCUMENTS Examiner Initial OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.	dy	5	8	4	0	1	9	9	11/24/98	Warre	n	216	2	4/8/9	n	
FOREIGN PATENT DOCUMENTS Examiner Initial Document Number Date Country Class Subclass Partial Translation Yes No OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.	Sus	5	7	5	6	2	5	6		Nakati	o, et al.	430	272.1	1/16	197	
FOREIGN PATENT DOCUMENTS Examiner Initial Document Number Date Country Class Subclass Partial Translation Yes No OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.		<u> </u>					<u> </u>		 							
FOREIGN PATENT DOCUMENTS Examiner Initial Document Number Date Country Class Subclass Partial Translation Yes No OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.		<u> </u>		_					<u> </u>			050	L			
FOREIGN PATENT DOCUMENTS Examiner Initial Document Number Date Country Class Subclass Partial Translation Yes No OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.		-	ļ			_	<u> </u>		<u> </u>	ļ		EIVE	IVED			
FOREIGN PATENT DOCUMENTS Examiner Initial Document Number Date Country Class Subclass Partial Translation Yes No OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.		<u> </u>					<u> </u>		D -			FFR (7 2002	-		
FOREIGN PATENT DOCUMENTS Examiner Initial OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.		╂		-			_	-	TEO,	_	70	ŀ	1	1		
FOREIGN PATENT DOCUMENTS Examiner Initial OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.		<u> </u>		-	-			<u> </u>	WAL C	110	(0)	Unnology	Center 2	00_		
FOREIGN PATENT DOCUMENTS Examiner Initial OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.		<u> </u>		<u> </u>	ļ	<u> </u>		_ ;	10	2	D	<u> </u>				
Examiner Initial Document Number Date Country Class Subclass Partial Translation Yes No OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.		ļ <u>.</u>							<u>L'75</u>	102						
Examiner Initial Document Number Date Country Class Subclass Partial Translation Yes No OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.									. 7	20						
Examiner Initial Document Number Date Country Class Subclass Partial Translation Yes No OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.																
Translation Yes No OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.								FOF	REIGN PAT	ENT D	OCUMENTS					
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.) Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.									Date Count		,	Class	Subclass			
Toyoshima, Toshiyuki, et al. "01. µm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.														Yes	No	
Toyoshima, Toshiyuki, et al. "01. μm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.	1															
Toyoshima, Toshiyuki, et al. "01. μm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.	+-	1	<u> </u>													
Toyoshima, Toshiyuki, et al. "01. μm Level Contact Hole Pattern Formation with KrF Lithography by Resolution Enhancement Lithography Assisted by Chemical Shrink (RELACS)," IEDM 98 333-336.	+-	<u> </u>	L	<u> </u>	L	HFR	ART	\ \{\nch	uding Autho	r. Title	Date. Pertinent l	Pages, etc.	<u> </u>	L		
EXAMINER MOCHET DATE CONSIDERED 9/30/03	اما	KrF I	Litho	grapl	shiyi iy by	ıki, e Res	t al. oluti	"01. on E	μm Leve	l Conta	ct Hole Pattern	Formati	on with			
examiner sulactions date considered 9/30/03		-												J 	······································	
• ·	EXAMI	NER	ÅR.	Nac	Av	b	>			DA'	TE CONSIDERE	9/3	30/0	3_		

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Informati n Disclosure Statement PTO-1449 (Modified)

The identification of any reference is not intended to be, and should not be understood as being, an admission that such publication, in fact, constitutes "prior art" within the meaning of applicable law since, for example, a given reference may have a later effective date than first seems apparent or the reference may have an effective date which can be antedated. The "prior art" status of any reference is a matter to be resolved during prosecution.

SHEEL	1	O1	1

Form PTO-1449 (Modified) P EIST OF PATENTS AND PUBLICATIONS										Atty. Docket No E0808	Serial No.: 09/973,240				
61 P	FILE	701			AND PLIC			TIONS		Applicants: Ran	۸.	1. 13			
HOV 1	INEC				CLOS sheets if		sary)	FEMENT		Filing Date: October 9, 2001	1756	<u></u>			
TENTA IB	OEM						R	EFERENC	E DESI	GNATION U.S.	PATEN	r Docum	1ENTS		
Examiner Initial		ument N	lumber			•		Date	Name Class			Subclass	ass Filing Date if Appropriate		
Sm	6	2	2	1	5	6	2	4/24/01	Boyd,	et al	430	314	11/13	/98	
An	6	1	0	7	1	7	2	8/22/00	Yang,	et al.	438	585	8/1/9	,	
DUN	5	2	9	4	2	9	1	3/15/94	Akahos	hi, et al.	156	637	9/21/	92	
des	4	2	2	4	3	6	1	9/23/80	Roman	kiw	427	259	9/5/78	8	
hon	4_	1	1	9	4	8	3 -	10/10/78	Hubsch	, et al.	156	655	2/8/7	,	
	10	0	3	3	9	9	8	10/25/01	Fujio				3/6/0	1	
									Ĺ						
Possina	T						FOR	EIGN PAT	T	OCUMENTS	Class	Substan	Partial		
Examiner Initial	Docu	Document Number							Country		CIASS	Subclass	Transl		
				,									Yes	No	
M	4	2	5	9	5	7	A2	5/8/91	Europe		H01L	21/311			
hr	7	5	3	7	6	4	Al	1/15/97	Europe		G02B	1/10		·	
/ 				<u> </u>	!			I							
				OT	HER	ART	(Inclu	ding Autho	r, Title	Date, Pertinent P	ages, etc.)	1		
1		ationa	ıl Sea	rch R	eport										
9 1	Intern										· · · · · · · · · · · · · · · · · · ·		1		
m	Intern														
9 1	Intern									<u> </u>]		
hr													J .		
9 1		mi	 aca						DA	TE CONSIDEREI	9/3	193			

if not in conformance and not considered. Include copy of this form with next communication to applicant.

<u>Information Disclosure Statement PTO-1449 (Modified)</u>

The identification of any reference is not intended to be, and should not be understood as being, an admission that such publication, in fact, constitutes "prior art" within the meaning of applicable law since, for example, a given reference may have a later effective date than first seems apparent or the reference may have an effective date which can be antedated. The "prior art" status of any reference is a matter to be resolved during prosecution.